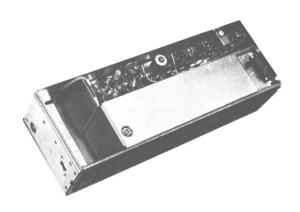
# ASTR Imperial

450-470 MHz, 30 WATT TRANSMITTER MODEL 4KT16B10



# SPECIFICATIONS \*

FCC Filing Designation

Frequency Range

Power Output

Crystal Multiplication Factor

Frequency Stability

Spurious and Harmonic Radiation

Modulation

Audio Frequency Characteristics

Distortion

Modulation Sensitivity

Maximum Frequency Spacing

Duty Cycle

KT-16-B

450-470 MHz

30 Watts (Adjustable from 10 to 30 Watts)

36

 $\pm .0002\%$  (-30°C to +60°C)

At least 70 dB below rated power output

Adjustable from 0 to ±5 kHz swing with instantaneous modulation

limiting.

octave pre-emphasis from 300 to 3000 Hz per EIA standards. Post limiter filter per FCC and EIA.

Within +1 dB to -3 dB of a 6-dB/

Less than 3%

50 to 100 Millivolts

 $\pm 0.2\%$ 

EIA 20% Intermittent

<sup>\*</sup>These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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#### — WARNING —

No one should be permitted to handle any portion of the equipment that is supplied with voltage or RF power; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

## **DESCRIPTION**

Transmitter Model 4KT16Bl0 is a crystal controlled, frequency modulated transmitter designed for one through four-frequency operation in the 450 to 470 megahertz band. The transmitter consists of the following assemblies:

- Exciter Board A101
   Transistorized audio, oscillator, modulator, amplifier and multiplier stages.
- Transistorized PA Assembly Amplifier/tripler, drivers and PA, low-pass filter and antenna relay.

## **CIRCUIT ANALYSIS**

The transmitter 4KT16B10 provides a power output of 30 Watts in the 450 to 470 MHz range. The frequency is determined by plug-in ICOM modules with ranges from approximately 12.5 to 13.6 megahertz, which is multiplied 36 times.

A centralized metering jack (J102) is provided for use with GE Test Set Models 4EX3A10 (Rev. A or later) or 4EX8K11. The test set meters the amplifiers, multipliers, driver PA stage, and PA supply voltages. The metering jack also provides access to receiver audio, microphone and push-to-talk leads.

All input leads to the transmitter are individually filtered by the 20-pin feed-through by-pass connector J101. Supply voltage, metering and control functions for the exciter board are connected from the PA assembly to jacks J1 through J18 on the exciter board.

#### EXCITER

#### ICOM MODULE

ICOM module Model 4EG25A10 consists of a crystal-controlled Colpitts oscillator, a voltage regulator, a Channel Guard tone modulator and a buffer output stage. The entire module (including crystal) is enclosed in a dust-proof aluminum can, with the ICOM frequency and the transmitter

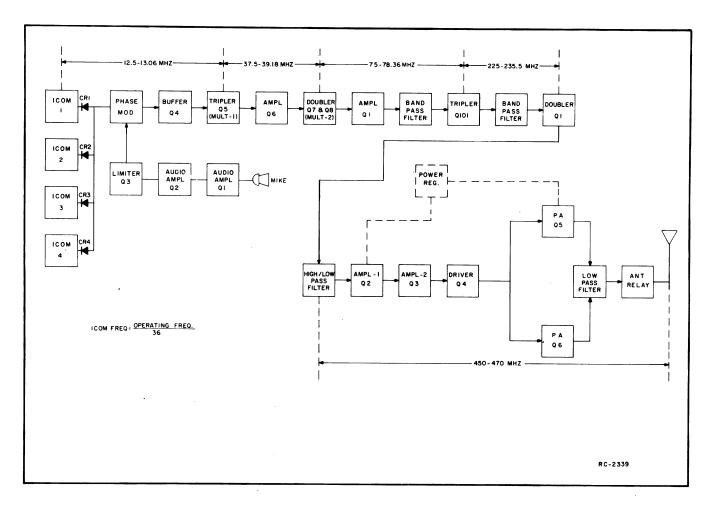


Figure 1 - Transmitter Block Diagram

operating frequency printed on the top. Access to the oscillator trimmer is obtained by prying off the plastic GE decal on the top of the can.

The oscillator frequency is temperature-compensated at both ends of the temperature range to provide instant frequency compensation, with a frequency stability of  $\pm .0002\%$ .

In single-frequency transmitters, a keying jumper (from R38 on the exciter board) connects the ICOM to ground. Keying the transmitter applies +10 Volts to the ICOM, turning it on. With the ICOM operating, diode CRl is forward biased and the oscillator output is applied to the modulator stage.

In multi-frequency transmitters, up to three additional ICOM modules can be plugged into the exciter board. The single-frequency keying jumper is removed, and the proper frequency is selected by switching the ICOM keying lead to ground by means of a frequency selector switch on the control unit.

#### -CAUTION-

All ICOM modules are individually compensated at the factory, and cannot be repaired in the field. Any attempt to remove the ICOM cover will void the warranty.

## AUDIO AMPLIFIERS AND LIMITER

The audio section of the transmitter consists of direct-coupled feedback amplifiers Q1, Q2 and Q3. Q3 also acts as a limiter at high audio input levels. Audio from the microphone is coupled through an input network (C2 and R1) to the audio stages. The input network, in conjunction with the feedback circuit, provides the audio gain and a 6-dB/octave pre-emphasis.

The output of limiter Q3 is connected through Modulation Adjust potentiometer R8 to a de-emphasis network for 6-dB/octave de-emphasis and post limiter roll-off. The network consists of C7, C8, C9, R15, R16 and R17. Modulation adjust R8 determines the maximum signal level applied to the modulator circuit, and is normally set for  $\pm 4.5$  kHz (narrow band).

## PHASE MODULATOR

The phase modulator uses varactor CV1 (a voltage-variable capacitor) in a R-L-C network that includes R20 and L1. An audio signal applied to the modulator through L1 varies the capacitance of CV1, resulting in a phase modulated output. The modulator output is coupled through C13 to the base of buffer Q4.

## BUFFER, AMPLIFIER AND MULTIPLIERS

Buffer stage Q4 isolates the modulator from the loading effects of the tripler stage, and provides some amplification. The output is direct-coupled to the base of Q5.

Q5 operates as a tripler (MULT-1) with the collector tank (T1) tuned to three times the ICOM frequency. The tripler is metered at J102 through R36. Following the tripler is amplifier Q6. This stage is metered at J102 through R35. The output of Q6 is capacitive-coupled from T1 to T3, and then to the base of Q7 and Q8.

Q7 and Q8 operate as a class C, push-pull doubler (MULT-2) with the collector tank (T4) tuned to six times the ICOM frequency. The doubler stage is metered at J102 through R34.

#### POWER AMPLIFIER ASSEMBLY

The Power Amplifier Assembly consists of a 75 MHz amplifier and band-pass filter, a tripler and a 225 MHz band-pass filter, a doubler, a high/low-pass filter, two UHF amplifiers, a driver, a final P.A. stage, and a low pass filter. The assembly is completely solid state, and the band pass-filters are tuned prior to assembly. No tuning adjustments are required to the Power Amplifier Assembly.

#### ---WARNING---

The stud mounted RF Power Transistors used in the transmitter contain Beryllium Oxide, a TOXIC substance. If the ceramic or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

## AMPLIFIER/TRIPLER A102

The exciter output is coupled to the base of 75-78.36 MHz amplifier Al02-Q1. This stage operates as a common-emitter broad band amplifier and is coupled to pretuned 75-78.36 MHz band-pass filter FL101. The output of this filter is metered at centralized metering jack J102 through voltage divider R6 and R7.

Following the 75-78.36 MHz band-pass filter is tripler Al02-Q101. Q101 is a common-emitter amplifier with its collector coupled to pretuned 225-235 MHz band-pass filter FL102. The output of this filter is metered through R2 on Power Amplifier board Al03.

POWER AMPLIFIER A103

#### -CAUTION-

The length, width, and bonding of the micro strips and the placement of components on the P.A. assembly boards is critical to the performance of the transmitter. Alteration of these parameters should be avoided.

The output of the 225-235 band-pass filter is coupled to doubler Al03-Ql. Ql is a common-emitter amplifier with its output applied to a high/low-pass filter. This doubler stage increases the frequency to 36 times the ICOM frequency, which after filtering is applied to the base of the 1st UHF Amplifier Al03-Q2. Q2, the 2nd UHF Amplifier Al03-Q3 and the driver amplifier Al03-Q4, are common-emitter operated broad band amplifiers. The output of driver Q4 is capacitive-coupled through a power splitting circuit to the bases of final transistors Al03-Q5 and Q6. The combined collector current of Q3 and Q4 is metered with the GE Test Set in position F.

Q5 and Q6 are separate common-emitter broad band power amplifiers. An equal amount of power from driver Al03-Q4 is applied through the power splitting circuit to their respective inputs. The power from their collectors is additively combined and is coupled through low-pass filter FL103 to antenna relay K901. Antenna relay K901 transfers power from the transmitter to the antenna when the transmitter is keyed.

The combined collector current of Q5 and Q6 is metered on the one Volt scale (10 amperes full scale) with the GE Test Set in Position G, and with the HIGH SENSITIVITY button pressed.

## CARRIER CONTROL TIMER

The Carrier Control Timer option shuts off the transmitter on each transmission after a one-minute timing cycle, and alerts the operator that the transmitter is off by means of an alert tone in the speaker. The transmitter can be turned on again by releasing and rekeying the push-to-talk switch on the microphone.

The timing cycle (transmitter keyed time) is normally set at the factory for a duration of one minute. An optional potentiometer is available that permits the timing cycle to be adjusted from 15 seconds to 5 minutes. Complete instructions for the Carrier Control Timer are contained in Maintenance Manual LBI-4138.

#### ANTENNA CUTTING INSTRUCTIONS

Install antenna Model 4EY12A13 according to instructions provided with the antenna. Cut the whip for 450-470 MHz operation as directed on the cutting chart.

## **MAINTENANCE**

#### **DISASSEMBLY**

To service the transmitter from the top (Figure 2):

- Pull locking handle down and pull radio about one inch out of mounting frame.
- 2. Pry up cover at rear of transmitter.
- 3. Slide cover back and lift off.

To service the transmitter from the bottom (Figure 3):

- 1. Pull locking handle down. Pull radio out of mounting frame.
- 2. Remove two screws in bottom cover.
  Pry up at back of transmitter.
- 3. Slide cover back and lift off.

To remove transmitter from system frame:

- Loosen the two retaining screws in the front casting (see Figure 2) and pull casting away from the system frame.
- Remove the four screws in the back cover.
- Remove the two screws holding the transmitter at each end of the system frame.
- 4. Disconnect the antenna plug and receiver plug in front of the transmitter and the 20-pin feed-through connector at the back of the transmitter, and slide the unit out of the system frame.

PA TRANSISTOR REPLACEMENT

#### ---WARNING-

The stud mounted RF Power Transistors used in the transmitter contain Beryllium Oxide, a TOXIC substance. If the ceramic or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

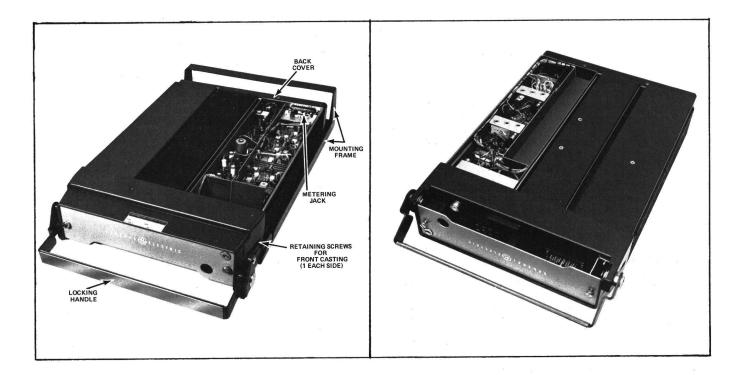


Figure 2 - Top Cover Removed

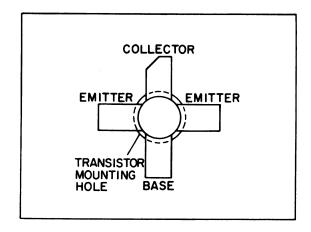
To replace the PA transistors (Q1 through Q6 on A103):

- 1. Remove the Amplifier/Tripler board Al02 from the transmitter. To remove Al02 it is necessary to remove the two screws holding Q101, the screws holding Al02 to the heat sink and leads connected to Al02.
- 2. Using a 50 Watt soldering iron lift the two emitter leads of the transistor to be replaced off the printed wire board. Hold the leads away from printed wire board pattern until the solder cools.
- 3. Remove the transistor hold-down nut and spring-washer through the hole in the heatsink with an 11/32-inch nut-driver.
- 4. Heat the base and collector leads simultaneously and lift out the transistor.
- 5. Remove the old solder from the printed circuit board with a desoldering tool such as a SOLDA PULLT.® Special care should be taken to prevent damage to the printed circuit board runs.
- 6. Trim the new transistor leads (if required) to the lead length of

Figure 3 - Bottom Cover Removed

the removed transistor. Cut the collector lead at a  $45^{\circ}$  angle for future identification (see Figure 4). The letter "C" on the top of the transistor indicates the collector.

- 7. Apply a coating of silicone grease around the transistor mounting surface, and place the transistor in the mounting hole. Align the leads as shown in the Outline Diagram. Then hold the body of the transistor and replace the holding-down nut and spring-washer, using moderate torque (6-8-inch-pounds). A torque wrench must be used for this adjustment since transistor damage can result if too little or too much torque is used.
- 8. Make sure that the transistor leads are formed as shown in Figure 5 so that the leads can be soldered to the printed circuit pattern, starting from the inner edge of the mounting hole
- 9. Solder the leads to the printed circuit pattern. Start at the inner edge of mounting hole and solder the remaining length of transistor lead to the board. Use care not to use excessive heat that causes the printed wire board runs to lift up from the board. Check for shorts and solder bridges before applying power.



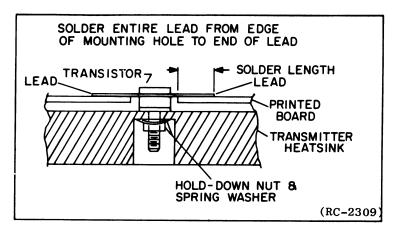


Figure 4 - Lead Identification

Figure 5 - Lead Forming

-CAUTION-

Failure to solder the transistor leads as directed may result in the generation of RF loops that could damage the transistor or may cause low power output.

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# **MODULATION LEVEL ADJUSTMENT**

The MOD ADJUST (R8) was adjusted to the proper setting before shipment and should not normally require readjustment. This setting permits approximately 75% modulation for the average voice level. The audio peaks which would cause overmodulation are clipped by the modulation limiter. The limiter, in conjunction with the de-emphasis network, instantaneously limits the slope of the audio wave to the modulator, thereby preventing overmodulation while preserving intelligibility.

#### TEST EQUIPMENT

- 1. An audio oscillator (GE Model 4EX6A10)
- 2. A frequency modulation monitor
- 3. An output meter or a VTVM
- 4. GE Test Set Models 4EX3AlO or 4EX8KlO

# PROCEDURE

- 1. Connect the audio oscillator and the meter across audio input terminals J5 (Green-Hi) and J6 (Black-Lo) on GE Test Set or across J1 (Mike High) and J2 (Mike Low) on the Exciter Board.
- 2. Apply a 0.75-Volt signal at 1000 Hz to Test Set or across J1 and J2 on Exciter Board.
- 3. For transmitters without Channel Guard, set the MOD ADJUST (R8) for a 4.5-kilohertz swing with the deviation polarity which gives the highest reading as indicated on the frequency modulation monitor.
- 4. For transmitters with Channel Guard, set the Channel Guard MOD ADJUST (R25) for 0.75 kHz tone deviation. Remove the tone to the transmitter by unplugging leads to J8 and J9 on Exciter Board, or by switching to a non-Channel Guard frequency in multifrequency units. Next, apply a 0.75-Volt signal at 1000 Hz and set MOD ADJUST (R8) for a 3.75 kHz deviation (4.5 kHz minus 0.75 kHz tone deviation).
- 5. For multi-frequency transmitters, set the deviation as described in Steps 3 and 4 on the channel producing the largest amount of deviation.

## PA POWER INPUT

For FCC purposes, the PA power input can be determined by measuring the PA supply voltage and PA current, and using the following formula:

P<sub>i</sub> = PA voltage x PA current

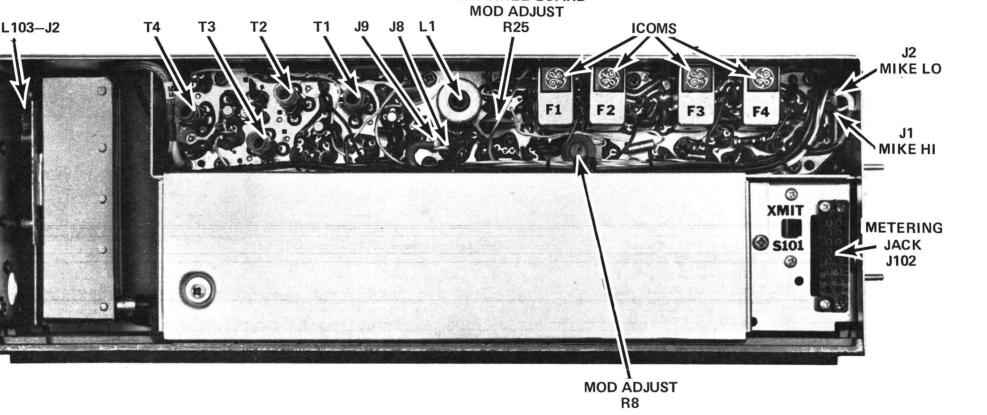
#### Wher

Pi is the power input in Watts,

PA voltage is measured with the GE Test Set in Position G on the 15 Volt scale, and the polarity switch in (-) position.

PA current is measured with the Test Set in Position G in the Test 1 position, and with the HIGH SENSITIVITY button pressed (10 amperes full scale).

Example:  $P_i = 12.6 \text{ Volts x } 5.0 \text{ amperes } -63 \text{ Watts}$ 



CHANNEL GUARD

## TRANSMITTER ALIGNMENT

#### EQUIPMENT REQUIRED

- 1. GE Test Set Model 4EX3AlO (Revision A or later), or Model 4EX8Kll.
- 2. A 50-ohm wattmeter connected to FL103-J2.

# PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Place ICOM (s) in proper socket (ICOM frequency = operating frequency ÷ 36). Do not adjust ICOM trimmer.
- 2. Set the channel selector switch to the F1 position.
- 3. Turn the power adjust potentiometer R13 on the power regulator board fully clockwise.
- 4. Turn the slugs in the Exciter coils L1, T1, T2, T3, and T4 to the bottom of the coil. When tuning these coils, select the first resonance as the tuning slug is rotated counter-clockwise out of the coil.
- 5. Connect the GE Test Set to Receiver Metering Jack J442 and check for +10 Volts at Position J. If reading is not 10 Volts, refer to the Power Regulator Outline Diagram and set R28 for +10 Volts.
- 6. Connect GE Test Set to Metering Jack J102. Set the test polarity to + and set the range to the Test 1 (or 1-Volt position for 4EX8K11).
- 7. All adjustments are made with the transmitter keyed and supplied with 13.6V at the battery end of the Power Cable. Unkey the transmitter between steps to avoid unnecessary heating.

## TRANSMITTER ALIGNMENT PROCEDURE

STEP	METER POSITION	TUNING CONTROL	METER READING	PROCEDURE				
	EXCITER BOARD							
1.	A MULT-1	L1 & T1	See Procedure	Carefully tune Ll for maximum meter reading. Tune Tl for a small change in meter reading.				
2.	B AMP-1	T1 & T2	See Procedure	Tune Tl for maximum meter reading. Tune T2 for a dip in meter reading.				
3.	C MULT-2	T3, T2 & T4	See Procedure	Adjust T3 for maximum meter reading. Re-adjust T2 for maximum meter reading. Then adjust T4 for minimum meter reading.				
4.	D AMP-2	T4	See Procedure	Carefully tune T4 for maximum meter reading.				
	POWER AMPLIFIER							
5.		R13		Turn potentiometer R13 on the power regulator to set the transmitter power out for the desired power (between 10 and 30 watts).				
			NOTE: Coils Al05-L8 (Amplifier/Tripler) and Al03-L4 (Power Amplifier) have been adjusted at the factory and normally require no further adjustment. If in some way L8 or L4 is bent the following pro- cedure should be used.					
6.			Disconnect cable W2 and connect a 50-ohm wattmeter (1.2 Watt scale) to FL102-J2.					
7.			Repeat preliminary steps 2 and 3.					
8.		L8		If the power output of AlO5 is less than 0.4 Watt, slightly spread or compress coil AlO5-L8 to obtain 0.4 W minimum				
9.				Remove the wattmeter from FL102-J2 and re-connect cable W2.				
10.		L4 .		If the transmitter power output is less than 30 Watts, spread or compress AlO3-L4 until 30 Watts minimum is obtained.				
11.				Repeat step 5.				

# FREQUENCY ADJUSTMENT

First, check the transmitter frequency to determine if any adjustment is required. The frequency should be checked with a frequency meter or counter having an accuracy of 0.4 partper-million (PPM), and with the ICOM module at 80°F (±4°F) or 26.5°C (±2°C) when possible. The ICOM temperature can be determined by taping a mercury thermometer to the side of the

NOTE: To prevent radiated RF from causing the electronic counter to malfunction, the transmitter must be shielded or the counter must be approximately 10 feet from the transmitter.



The ICOM case is at +10 Volts DC. Be careful not to short the case to ground.

If an adjustment is required, use one of the following procedures:

If the ICOM is stabilized at  $80^{\circ}$  F, pry off the GE emblem and adjust the ICOM trimmer for correct transmitter operating frequency.

If the ICOM is not stabilized at 80° F, pry off the GE emblem and check for a color dot on the top of the can. This color dot indicates which correction curve to use in setting the unit on frequency (see Figure 6). Next, tape a thermometer to the ICOM and check the temperature when the thermometer is stabilized. Then proceed as shown in the following example:

- 1. Assume that the ICOM is marked with a green color dot and the temperature reading is 50° F. At that temperature, the green curve shows a correction factor of approximately +1.5 PPM. (At 450 MHz, 1 PPM is 450 Hz. At 470 MHz, 1 PPM is 470 Hz.)
- With a transmitter operating frequency of 450 MHz, adjust the ICOM trimmer for a reading of +675 Hz (+1.5 x 450) <u>higher</u> than the licensed operating frequency.
- 3. If a negative correction factor is obtained (at temperatures above 80° F), adjust the ICOM trimmer for the indicated PPM lower than the operating frequency.

#### DEGREES CENTIGRADE

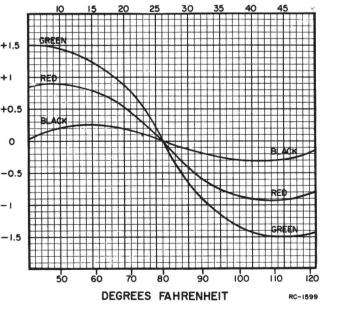


Figure 6 - ICOM Frequency Correction Curve

# ALIGNMENT PROCEDURE

LBI-4386

450—470 MHz, 30-WATT TRANSMITTER MODEL 4KT16B10

LBI-4386

# **TEST PROCEDURES**

These Test Procedures are designed to assist you in servicing a transmitter that is operating-but not properly. Problems encountered could be low power output, low B plus, tone and voice deviation, defective audio sensitivity and modulator adjust control set too high. By following the sequence of test steps starting with Step 1, the

defect can be quickly localized. Once a defect is pin-pointed, refer to the "Service Check" and the additional corrective measures included in the Transmitter Troubleshooting Procedure. Before starting with the Transmitter Test Procedures, be sure the transmitter is tuned and aligned to the proper operating frequency

# TEST EQUIPMENT REQUIRED

for test hookup as shown:

1. Wattmeter similar to: 2. VTVM similar to: 3. Audio Generator similar to: 4. Deviation Meter (with a

Bird # 43 Jones # 711N Triplett # 850 Heath # 1M-21

GE Model 4EX6AlO or Heath # 1G-72

.75 kHz scale) similar to:

Measurements # 140 Lampkin # 205A

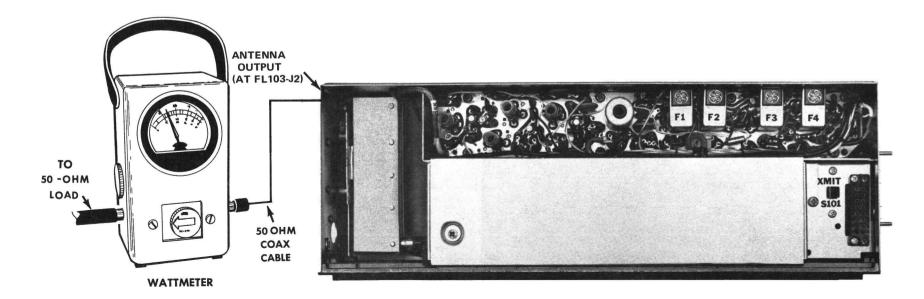
5. Multimeter similar to:

GE TEST SET MODEL 4EX3A10. MODEL 4EX8K11 or 20,000 ohms-per-volt voltmeter

# STEP 1

# POWER MEASUREMENT **TEST PROCEDURE**

1. Connect transmitter output to wattmeter as shown below:



2. Key transmitter and check wattmeter for minimum reading of 30 Watts when power adjust pot R13 is fully clockwise.

# SERVICE CHECK

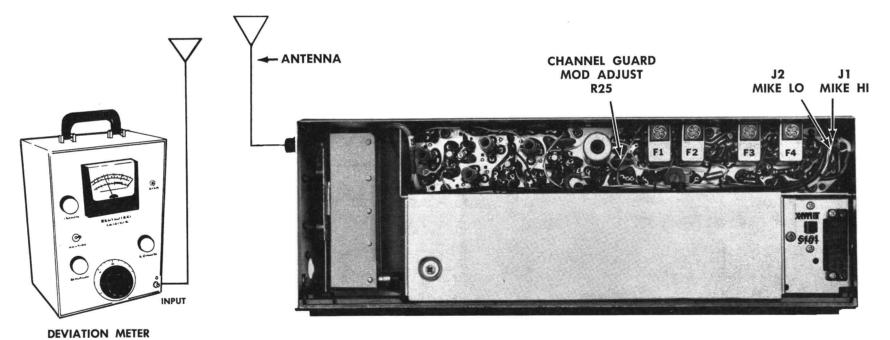
Refer to Service Hints on Transmitter Troubleshooting Procedure.

Coax cables and connectors are lossy at UHF frequencies. Insure low power out is not caused by excessive loss in connections from transmitter to wattmeter. Use good, short, 50 ohm cables with properly installed connectors.

# STEP 2

# TONE DEVIATION WITH CHANNEL GUARD TEST PROCEDURE

1. Set up Deviation Meter and monitor output of transmitter as shown below:



- 2. Unplug the MIC HI terminal from Jl on Transmitter Exciter Board.
- 3. Key transmitter and check for 0.75-kHz deviation. If reading is low or high, adjust Channel Guard MOD ADJUST (R25) for a reading of 0.75-kHz.

NOTES:--The Channel Guard MOD ADJUST (R25) may be adjusted for deviations up to 1.0 kHz maximum for all tone frequencies.

- 1. On units supplied with Channel Guard, the Phase Modulator Tuning should be peaked carefully to insure proper performance. (Refer to Steps 1 in the Transmitter Alignment Chart).
- 2. The Tone Deviation Test Procedures should be repeated every time the Tone Frequency is changed.

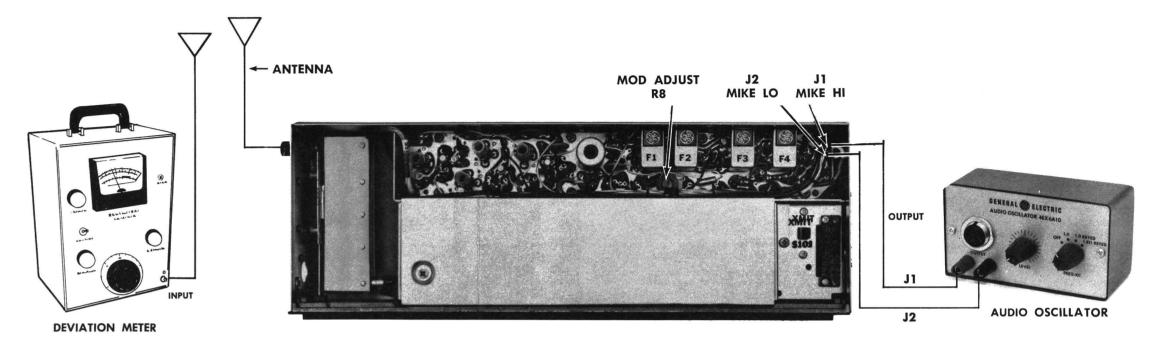


DEVIATION METER

# STEP 3

# **VOICE DEVIATION AND SYMMETRY TEST PROCEDURE**

- 1. Unplug the High and Low Mike leads from the Exciter Board Jacks Jl and J2.
- 2. Connect test equipment to transmitter as shown below:



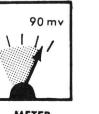
- 3. Set the generator output to 0.75 VOLTS RMS and frequency to 1 kHz.
- 4. Key the transmitter and adjust Deviation Meter to carrier frequency
- 5. Deviation reading should be  $\pm 4.5$  kHz.
- 6 Adjust Modulation Adjust Control R8 until deviation reads 4.5 kHz on plus (+) or minus (-) deviation, whichever is greater. This adjustment should be made with the correct level of tone applied on Channel Guard transmitters.



NOTES: --MASTR transmitters are adjusted for 4.5 kHz deviation at the factory. The factory adjustment will prevent the transmitter from deviating more than 5.0 kHz under the worst conditions of frequency, voltage and temperature.

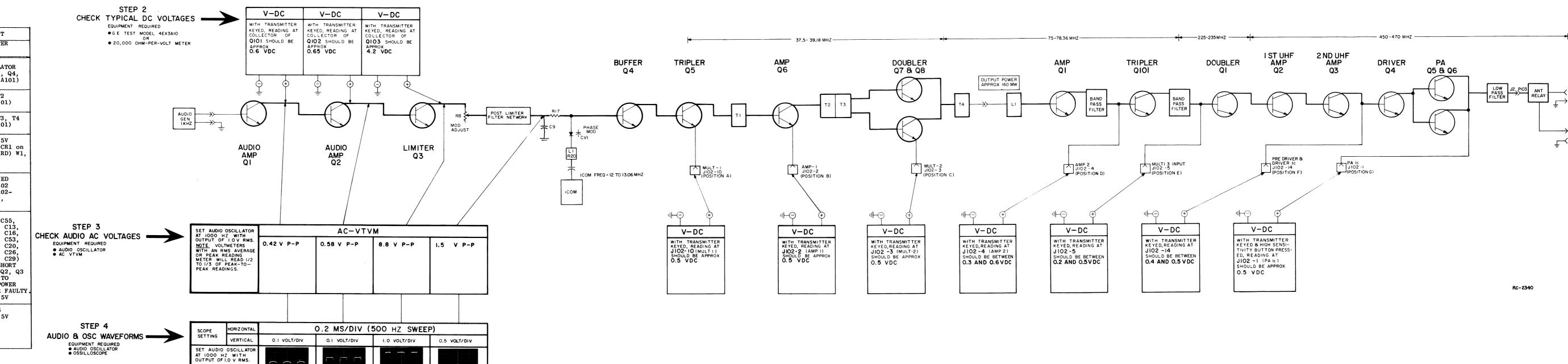
If the deviation reading plus (+) or minus (-) differs by more than 0.5 kHz, check the following:

- 1. Recheck Step 1 as shown in the Transmitter Alignment Chart.
- 2. Check Audio Sensitivity by reducing generator output until deviation falls to 3.0 kHz. Voltage should be LESS than 100 millivolts.



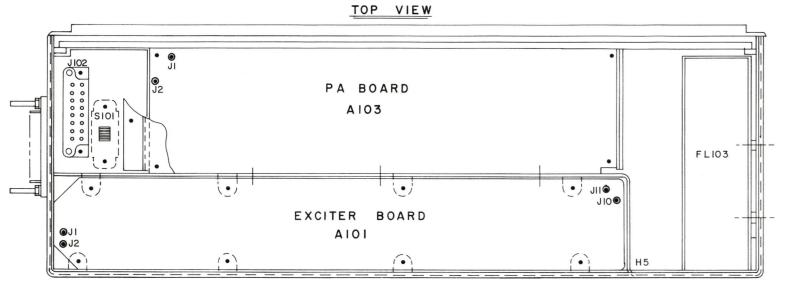
STEP I - QUICK CHECKS

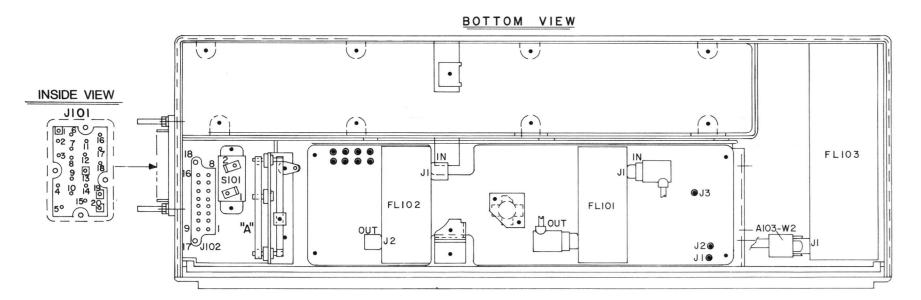
	PROBABLE DEFECTIVE STAGE OR COMPONENT					
METER POSITION	HIGH METER READING	LOW METER READING	ZERO METER READING			
A (MULT-1)	Q4 or Q5 (BOARD A101)	Q4 or open L1 (BOARD A101)	10V REGULATOR ICOM, CV1, Q4, Q5(BOARD A101)			
B (AMP 1)	Q6, T2 (BOARD A101)	Q6, T1 (BOARD A101)	T1, Q6, T2 (BOARD A101)			
C (MULT-2)	Q7, Q8, T4 (BOARD A101)	Q7, Q8, T3 (BOARD A101)	Q7, Q8, T3, T4 (BOARD A101)			
D (AMP-2)	Q101 (BOARD A102)	Q1 (BOARD A102) KEYED 12.5V A101- T4, FL101, W1, W2	KEYED 12.5V Q1 DIODE CR1 on (A102 BOARD) W1, W2			
E (MULT-3)		COIL L8 MIS- ALIGNED, Q101 (BOARD A102) A102-W3, FL102, A103-W1	Q101, KEYED 12.5V (A102 BOARD) A102- W3, FL102, A103-W1			
F (Pre Dr. + DRIVER IC)	Q3, Q4 COLLECTORS SHORTING TO GROUND C29, C35 SHORTING TO GROUND	L4 MISALIGNED POWER REGULA- TOR NOT SET RIGHT OR FAUL- TY - Q1, Q2, Q3, Q4	(C7, C9, C55, C10, C11, C13, C14, C15, C16, C51, C17, C53, C52, C18, C20, C24, C25, C26, C31, C30, C29) OPEN OR SHORT BASES OF Q2, Q3 SHORTING TO GROUND. POWER REGULATOR FAULTY. KEYED 12.5V			
G PA IC	Q5, Q6 COLLECTORS SHORTING TO GROUND. C42, C49 SHORTING TO GROUND	Q5 or Q6 FAULTY	Q5 and Q6 KEYED 12.5V			



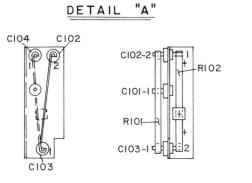
# TROUBLESHOOTING PROCEDURE

450-470 MHz, 30-WATT TRANSMITTER MODEL 4KT16B10





RUNS ON SOLDER SIDE



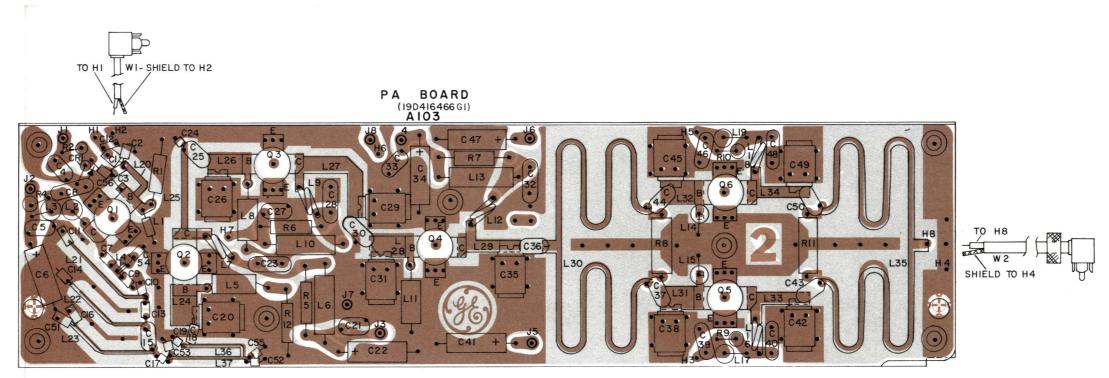
# OUTLINE DIAGRAM

450-470 MHz, 30-WATT TRANSMITTER MODEL 4KT16B10

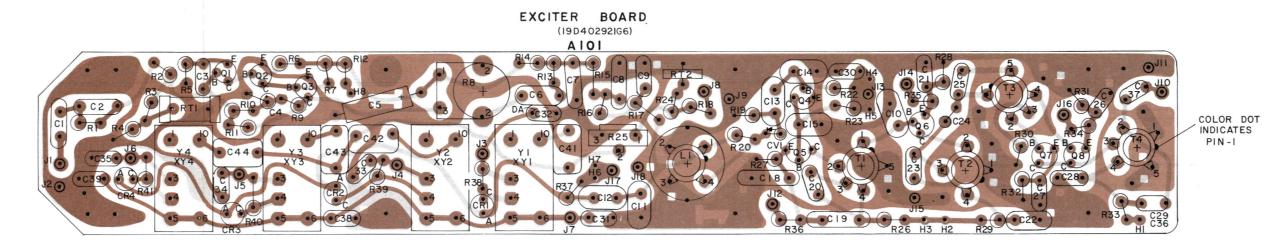


LEAD IDENTIFICATION FOR Q1 THRU Q8 EXCITER BD. ONLY

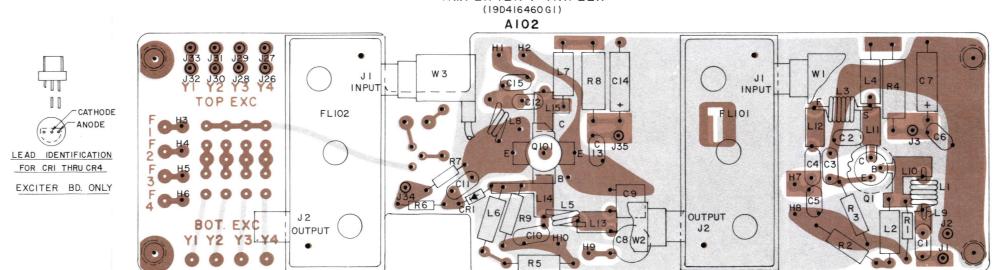
(19R621941, Rev. 1)



(19D416514, Sh. 1, Rev. 2) (19D416514, Sh. 2, Rev. 2)



AMPLIFIER / TRIPLER
(19D416460GI)



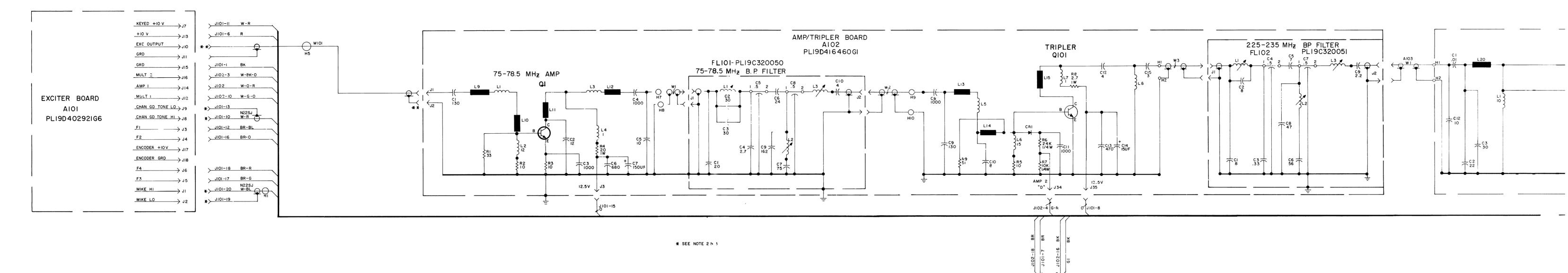
(19R621772, Rev 2)

LBI-4386

MULT-2 → JI6 AMP I >JI4 MULT-I >JI2 CHAN. GD. TONE LO J9 CHAN. GD. TONE HI > J8 ENCODER +IOV >JI7 ENCODER GND > JI8 <del>- F3</del>>J5 MIKE HI > JI

SCHEMATIC DIAGRAM

450-470 MHz, 30-WATT TRANSMITTER MODEL 4KT16B10 EXCITER)

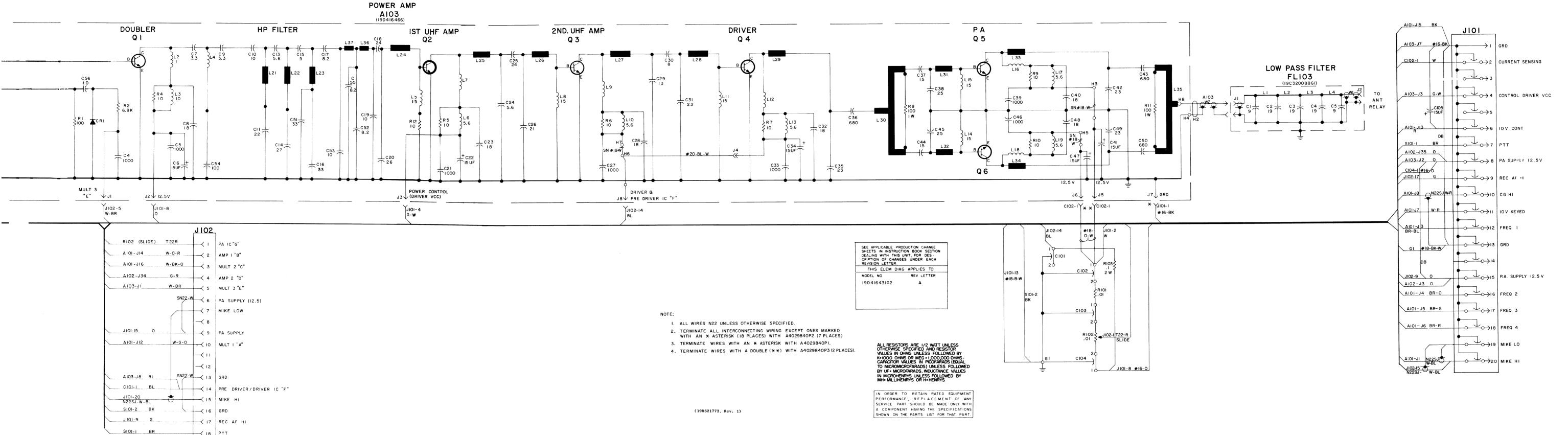


(19R621773, Rev. 1)

# SCHEMATIC DIAGRAM

450-470 MHz, 30-WATT TRANSMITTER MODEL 4KT16B10 (PA)

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# SCHEMATIC DIAGRAM

450-470 MHz, 30-WATT TRANSMITTER MODEL 4KT16B10(PA)

PARTS LIST LBI-4385A 450-470 MHz TRANSMITTER MODEL 4KT16B10 SYMBOL | GE PART NO.

DESCRIPTION

SYMBOL GE PART NO. DESCRIPTION 19A116080P1 Polyester: 0.01 µf ±20%, 50 VDCW. 7491395P111 Ceramic disc: 1500 pf ±10%, 500 VDCW; sim to RMC Type JL. C3 5494481P111 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C5 5496267P10 Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D. C6 19A116080P5 Polyester: 0.047 µf ±20%, 50 VDCW. 7491395P111 Ceramic disc: 1500 pf ±10%, 500 VDCW; sim to RMC Type JL. Ceramic disc: 1000 pf ±10%, 500 VDCW; sim to RMC Type JL. C9 7491395P109 C10 5493366P68K Mica: 68 pf ±10%, 100 VDCW; sim to Electro Motive Type DM-15. Cll 5493366P150J Mica: 150 pf ±5%, 100 VDCW; sim to Electro Motive Type DM-15. Cl2 5493366P150K Mica: 150 pf ±10%, 100 VDCW; sim to Electro Motive Type DM-15. Mica: 220 pf ±10%, 100 VDCW; sim to Electro Notive Type DM-15. Mica: 39 pf ±10%, 100 VDCW; sim to Electro Motive Type DM-15. C15 5493366P39K Ceramic disc: 3900 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Ceramic disc: 27 pf ±5%, 500 VDCW, temp coef -80 PPM. C20 5496219P249 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. C21 5494481P111 C22 5490008P127 Silver mica: 100 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15. Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM. C2? 5496219P250 C24 5491601P110 Phenolic: 0.36 pf ±5%, 500 VDCW. Ceramic disc: 27 pf ±5%, 500 VDCW, temp coef -80 PPM. 5496219P249 Ceramic disc: 1000 pf  $\pm 20\%$ , 1000 VDCW; sim to RMC Type JF Discap. C26 5494481P111 c28 Ceramic disc: 3.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM. C29 5496219P234 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Ceramic disc: 6.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM. Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. R35 R37 - - - - - DIODES AND RECTIFIERS - - - -19A115603P1 Silicon: 33 pf ±10%, 4 VDC; sim to Pacific Semi-conductors Varicap Type V-596. CV1 5495769P9

\*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

1				
	JACKS AND RECEPTACLES	R38 thru	3R77P272K	Composition: 2700 ohms ±10%, 1/2 w.
4033513P4	Contact, electrical: sim to Bead Chain L93-3.	R41		
	INDUCTORS	RT1	5490828P40	Thermistor: 10,000 ohms ±10%, color code red/white; sim to Globar Type 783-H.
19D402808G30	Coil. Includes:	RT2	19C300048P8	Disc: 2500 ohms ±10%; sim to GE 4D.
5491798P2	Tuning slug.	""	190300048F8	Disc. 2500 ones 110%; sim to de 40.
19A115889P1	Silicon NPN.	Tl	19D402808G32	Coil, Includes:
194113669P1	Silicon, MPN.	1 1	5491798P2	Tuning slug.
		Т2	19D402808G31	Coil. Includes:
19A115330P1 19A115328P1	Silicon, NPN.		5491798P2	Tuning slug.
19411532691	Silicon, NPN.	Т3	19D402808G33	Coil, Includes:
19A116201P1		i I	5491798P3	Tuning slug.
19A116201P1	Silicon, NPN.	Т4	19D402808G34	Coil. Includes:
			5491798P5	Tuning slug.
	RESISTORS		1	
3R77P204J	Composition: 0.20 megohm ±5%, 1/2 w.		İ	OSCILLATORS
3R77P562K	Composition: 5600 ohms ±10%, 1/2 w.			When reordering, specify ICOM Frequency.
3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.	1 1	ł	ICOM Frequency = (OF + 36).
		Y1 thru	4EG25A10	Integrated Circuit Oscillator Module (ICOM).
3R77P681K	Composition: 680 ohms ±10%, 1/2 w.	Y4	19D413070P1	Cap. decorative.
3R77P104K	Composition: 0.10 megohm ±10%, 1/2 w.			
3R77P393K	Composition: 39,000 ohms ±10%, 1/2 w.	11	1	SOCKETS
19B209358P6	Variable, carbon film: approx 75 to 10,000 ohms ±20%, 0.25 w; sim to CTS Type U-201.	XY1 thru	19B216043G1	Socket.
3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w.	XY4	1	
		A102		AMPLIFIER TRIPLER BOARD
3R77P565J	Composition: 5.6 megohms ±5%, 1/2 w.	<b>   </b>		19D416460G1
3R77P470K	Composition: 47 ohms ±10%, 1/2 w.	11		
3R77P623J	Composition: 62,000 ohms ±5%, 1/2 w.	C1	19A116114P69	Ceramic: 130 pf ±5%, 100 VDCW; temp coef
3R77P623J 3R77P513J	Composition: 62,000 ohms ±5%, 1/2 w.  Composition: 51,000 ohms ±5%, 1/2 w.	l I	1	Ceramic: 130 pf ±5%, 100 VDCW; temp coef 0 PPM.
		C1 C2	19A116114P69	Ceramic: 130 pf ±5%, 100 VDCW; temp coef 0 PPM. Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.
3R77P513J	Composition: 51,000 ohms ±5%, 1/2 w.	l I	1	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to
3R77P513J 3R77P393J	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w.	C2	19A116656P12J0	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef
3R77P513J 3R77P393J 3R77P473J	Composition: 51,000 ohms 15%, 1/2 w. Composition: 39,000 ohms 15%, 1/2 w. Composition: 47,000 ohms 15%, 1/2 w. Composition: 56,000 ohms 10%, 1/2 w.	C2 C3 and C4	19A116656P12J0	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef O PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
3R77P513J 3R77P393J 3R77P473J 3R77P563K	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w.	C2 C3 and C4 C5	19A116656P12J0 19A116655P19 19A116656P10G0	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef O PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef O PPM.
3R77P513J 3R77P393J 3R77P473J 3R77P563K 3R77P242J	Composition: 51,000 ohms ±5%, 1/2 w.  Composition: 39,000 ohms ±5%, 1/2 w.  Composition: 47,000 ohms ±5%, 1/2 w.  Composition: 56,000 ohms ±10%, 1/2 w.  Composition: 2400 ohms ±5%, 1/2 w.	C2 C3 and C4	19A116656P12J0	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef
3R77P513J 3R77P393J 3R77P473J 3R77P563K 3R77P242J 3R77P103K	Composition: 51,000 ohms ±5%, 1/2 w.  Composition: 39,000 ohms ±5%, 1/2 w.  Composition: 47,000 ohms ±5%, 1/2 w.  Composition: 56,000 ohms ±10%, 1/2 w.  Composition: 2400 ohms ±5%, 1/2 w.  Composition: 10,000 ohms ±10%, 1/2 w.	C2 C3 and C4 C5	19A116656P12J0 19A116655P19 19A116656P10G0	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 uf ±20%, 20 VDCW; sim to Sprague
3R77P513J 3R77P393J 3R77P473J 3R77P563K 3R77P242J 3R77P103K 3R77P223K	Composition: 51,000 ohms ±5%, 1/2 w.  Composition: 39,000 ohms ±5%, 1/2 w.  Composition: 47,000 ohms ±5%, 1/2 w.  Composition: 56,000 ohms ±10%, 1/2 w.  Composition: 2400 ohms ±5%, 1/2 w.  Composition: 10,000 ohms ±10%, 1/2 w.  Composition: 22,000 ohms ±10%, 1/2 w.	C2  C3 and C4  C5  C6  C7	19A116655P19 19A116655P19 19A116656P10G0 19A116655P17 5496267P14	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef o PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef o PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.
3R77P513J 3R77P393J 3R77P473J 3R77P563K 3R77P242J 3R77P103K 3R77P223K 3R77P233K	Composition: 51,000 ohms ±5%, 1/2 w.  Composition: 39,000 ohms ±5%, 1/2 w.  Composition: 47,000 ohms ±5%, 1/2 w.  Composition: 56,000 ohms ±10%, 1/2 w.  Composition: 2400 ohms ±5%, 1/2 w.  Composition: 10,000 ohms ±10%, 1/2 w.  Composition: 22,000 ohms ±10%, 1/2 w.  Composition: 33,000 ohms ±10%, 1/2 w.	C2 C3 and C4 C5	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 uf ±20%, 20 VDCW; sim to Sprague
3R77P513J 3R77P513J 3R77P473J 3R77P563K 3R77P242J 3R77P103K 3R77P223K 3R77P233K 3R77P333K	Composition: 51,000 ohms ±5%, 1/2 w.  Composition: 39,000 ohms ±5%, 1/2 w.  Composition: 47,000 ohms ±5%, 1/2 w.  Composition: 56,000 ohms ±10%, 1/2 w.  Composition: 2400 ohms ±5%, 1/2 w.  Composition: 10,000 ohms ±10%, 1/2 w.  Composition: 22,000 ohms ±10%, 1/2 w.  Composition: 33,000 ohms ±10%, 1/2 w.  Composition: 1500 ohms ±10%, 1/2 w.  Composition: 5100 ohms ±10%, 1/2 w.  Variable. carbon film: approx 75 to 25,000 ohms	C2  C3 and C4  C5  C6  C7	19A116655P19 19A116655P19 19A116656P10G0 19A116655P17 5496267P14	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef O PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef O PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sin to Sprague Type 150D.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sin to
3R77P513J 3R77P513J 3R77P473J 3R77P563K 3R77P242J 3R77P103K 3R77P223K 3R77P233K 3R77P152K 3R77P512J	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 5100 ohms ±10%, 1/2 w. Composition: 5100 ohms ±10%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201.	C2 C3 and C4 C5 C6 C7 C8	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef O PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef O PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sin to Sprague Type 150D.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.
3R77P513J 3R77P593J 3R77P473J 3R77P563K 3R77P242J 3R77P103K 3R77P223K 3R77P233K 3R77P152K 3R77P512J 198209358P107	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 5100 ohms ±10%, 1/2 w. Composition: 5100 ohms ±5%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19 19A116114P69 19A116656P8G0	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 1500.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic 130 pf ±5%, 100 VDCW; temp coef 0 PPM.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
3R77P513J 3R77P593J 3R77P473J 3R77P563K 3R77P242J 3R77P103K 3R77P233K 3R77P333K 3R77P512J 19B209358P107 3R77P390K	Composition: 51,000 ohms ±5%, 1/2 w.  Composition: 39,000 ohms ±5%, 1/2 w.  Composition: 47,000 ohms ±5%, 1/2 w.  Composition: 56,000 ohms ±10%, 1/2 w.  Composition: 2400 ohms ±5%, 1/2 w.  Composition: 10,000 ohms ±10%, 1/2 w.  Composition: 22,000 ohms ±10%, 1/2 w.  Composition: 33,000 ohms ±10%, 1/2 w.  Composition: 1500 ohms ±10%, 1/2 w.  Composition: 5100 ohms ±10%, 1/2 w.  Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201.  Composition: 39 ohms ±10%, 1/2 w.  Composition: 39 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19 19A116114P69	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; temp coef 0 PPM.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef
3R77P513J 3R77P393J 3R77P473J 3R77P563K 3R77P242J 3R77P103K 3R77P233K 3R77P233K 3R77P512J 19B209358P107 3R77P390K 3R77P30LJ	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 5100 ohms ±5%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 100 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19 19A116114P69 19A116656P8G0	O PPM.  Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef O PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to NMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef O PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to NMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to NMC Type JF Discap.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef O PPM.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef O PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to NMC Type JF Discap.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to NMC Type JF Discap.
3R77P513J 3R77P593J 3R77P473J 3R77P563K 3R77P263K 3R77P223K 3R77P233K 3R77P233K 3R77P512J 19B209358P107 3R77P390K 3R77P201J 3R77P101K	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±10%, 1/2 w. Composition: 200 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10 C11	19A116656P12J0 19A116655P19 19A116655P10 19A116655P17 5496267P14 19A116655P19 19A116114P69 19A116656P8G0 19A116655P19 19A116656P8G0	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 1500.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 1300 pf ±5%, 100 VDCW; temp coef 0 PPM.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
3R77P513J 3R77P393J 3R77P393J 3R77P473J 3R77P563K 3R77P242J 3R77P103K 3R77P23K 3R77P23K 3R77P512J 19B209358P107 3R77P390K 3R77P201J 3R77P101K 3R77P220K	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 5100 ohms ±5%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 100 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10 C11 C12 C13	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19 19A116114P69 19A116656P8G0 19A116655P19 19A116656P4G0 19A116655P13	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 8pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 8pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 4pf ±0.5 pf, 500 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; temp coef 0 PPM.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; temp coef 0 PPM.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; temp coef 0 PPM.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; temp coef 0 PPM.  Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
3R77P513J 3R77P593J 3R77P473J 3R77P565K 3R77P265K 3R77P223K 3R77P23K 3R77P23K 3R77P152K 3R77P512J 19B209358P107 3R77P390K 3R77P201J 3R77P101K 3R77P20K 3R77P100K	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 5100 ohms ±5%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±10%, 1/2 w. Composition: 200 ohms ±10%, 1/2 w. Composition: 20 ohms ±10%, 1/2 w. Composition: 20 ohms ±10%, 1/2 w. Composition: 10 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10 C11	19A116656P12J0 19A116655P19 19A116655P10 19A116655P17 5496267P14 19A116655P19 19A116114P69 19A116656P8G0 19A116655P19 19A116656P8G0	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 1500.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 8pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 8pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
3R77P513J 3R77P593J 3R77P473J 3R77P565K 3R77P265K 3R77P223K 3R77P23K 3R77P23K 3R77P152K 3R77P512J 19B209358P107 3R77P390K 3R77P201J 3R77P101K 3R77P20K 3R77P100K	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 5100 ohms ±5%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±10%, 1/2 w. Composition: 200 ohms ±10%, 1/2 w. Composition: 20 ohms ±10%, 1/2 w. Composition: 20 ohms ±10%, 1/2 w. Composition: 10 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10 C11 C12 C13	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19 19A116114P69 19A116656P8G0 19A116655P19 19A116656P4G0 19A116655P13	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sin to Sprague Type 150D.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; sin to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sin to Sprague Type 150D.  Ceramic disc: 3 pf ±0.5 pf, 500 VDCW; temp coef
3877P513J 3877P593J 3877P473J 3877P563K 3877P242J 3877P103K 3877P223K 3877P223K 3877P152K 3877P512J 198209358P107 3877P390K 3877P201J 3877P201J 3877P20K 3877P20K 3877P20K	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 5100 ohms ±10%, 1/2 w. Composition: 5100 ohms ±5%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 100 ohms ±10%, 1/2 w. Composition: 200 ohms ±10%, 1/2 w. Composition: 200 ohms ±10%, 1/2 w. Composition: 100 ohms ±10%, 1/2 w. Composition: 20 ohms ±10%, 1/2 w. Composition: 56 ohms ±10%, 1/2 w. Composition: 56 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10 C11 C12 C13	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19 19A116114P69 19A116656P8G0 19A116656P8G0 19A116656P4G0 19A116655P13	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 400 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.
3877P513J 3877P513J 3877P473J 3877P563K 3877P242J 3877P103K 3877P223K 3877P152K 3877P152K 3877P152L 198209358P107 3877P201J 3877P201J 3877P101K 3877P20K 3877P560K	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 5100 ohms ±10%, 1/2 w. Composition: 5100 ohms ±5%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w. Composition: 100 ohms ±10%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±10%, 1/2 w. Composition: 56 ohms ±10%, 1/2 w. Composition: 10 ohms ±10%, 1/2 w. Composition: 56 ohms ±10%, 1/2 w. Composition: 10 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10 C11 C12 C13	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19 19A116114P69 19A116656P8G0 19A116656P8G0 19A116656P4G0 19A116655P13	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sin to Sprague Type 150D.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; sin to RMC Type JF Discap.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW; sin to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sin to Sprague Type 150D.  Ceramic disc: 3 pf ±0.5 pf, 500 VDCW; temp coef
3877P513J 3877P513J 3877P473J 3877P473J 3877P263K 3877P224Z 3877P103K 3877P152K 3877P152L 198209358P107 3877P390K 3877P201J 3877P201J 3877P101K 3877P20K 3877P560K 3877P100K 3877P100K	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 5100 ohms ±10%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 100 ohms ±10%, 1/2 w. Composition: 22 ohms ±10%, 1/2 w. Composition: 10 ohms ±10%, 1/2 w. Composition: 56 ohms ±10%, 1/2 w. Composition: 10 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10 C11 C12 C13	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19 19A116114P69 19A116656P8G0 19A116656P8G0 19A116656P4G0 19A116655P13	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 4 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Ceramic disc: 3 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
3877P513J 3877P513J 3877P473J 3877P473J 3877P263K 3877P242J 3877P233K 3877P233K 3877P512J 198209358P107 3877P201J 3877P201J 3877P201J 3877P101K 3877P20K 3877P20K 3877P100K 3877P100K 3877P100K 3877P100K	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 1500 ohms ±10%, 1/2 w. Composition: 5100 ohms ±10%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 20 ohms ±10%, 1/2 w. Composition: 100 ohms ±10%, 1/2 w. Composition: 10 ohms ±10%, 1/2 w. Composition: 27,000 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10 C11 C12 C13 C14 C15	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19 19A116655P19 19A116655P19 19A116655P19 19A116655P19 19A116656P4G0 19A116656P4G0	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 1500.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 8pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 8pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 4pf ±0.5 pf, 500 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 4pf ±0.5 pf, 500 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 4pf ±0.5 pf, 500 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 4pf ±0.5 pf, 500 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 1500.  Ceramic disc: 3 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
3877P513J 3877P513J 3877P473J 3877P473J 3877P263K 3877P242J 3877P223K 3877P233K 3877P512J 198209358P107 3877P20LJ 3877P20LJ 3877P20LJ 3877P20LG 3877P20CG 3877P279C	Composition: 51,000 ohms ±5%, 1/2 w. Composition: 39,000 ohms ±5%, 1/2 w. Composition: 47,000 ohms ±5%, 1/2 w. Composition: 56,000 ohms ±10%, 1/2 w. Composition: 2400 ohms ±5%, 1/2 w. Composition: 10,000 ohms ±10%, 1/2 w. Composition: 22,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w. Composition: 5100 ohms ±10%, 1/2 w. Composition: 5100 ohms ±10%, 1/2 w. Variable, carbon film: approx 75 to 25,000 ohms ±10%, 0.25 w; sim to CTS Type X-201. Composition: 39 ohms ±10%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 200 ohms ±5%, 1/2 w. Composition: 22 ohms ±10%, 1/2 w. Composition: 10 ohms ±10%, 1/2 w. Composition: 56 ohms ±10%, 1/2 w. Composition: 10 ohms ±10%, 1/2 w. Composition: 47,000 ohms ±10%, 1/2 w. Composition: 27,000 ohms ±10%, 1/2 w. Composition: 27,000 ohms ±10%, 1/2 w.	C2 C3 and C4 C5 C6 C7 C8 C9 C10 C11 C12 C13 C14 C15	19A116656P12J0 19A116655P19 19A116656P10G0 19A116655P17 5496267P14 19A116655P19 19A116655P19 19A116655P19 19A116655P19 19A116655P19 19A116656P4G0 19A116656P4G0	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 1500.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 8pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 8pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.  Ceramic disc: 4pf ±0.5 pf, 500 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 4pf ±0.5 pf, 500 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 4pf ±0.5 pf, 500 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 4pf ±0.5 pf, 500 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 1500.  Ceramic disc: 3 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.

SYMBOL | GE PART NO.

DESCRIPTION

GE PART NO.  33513P4  33513P4  33513P4  8219456P1  88079P6  8219457P1  88079P6  8219457P2  D416451P1  A115329P1  77P330J  77P100J	DESCRIPTION	C15 C16 C17 C18 C19 C20 C21 C22 C23 C24 C25 C26 C27 C28 C29 C30 C31 C32	GE PART NO.  5496218P36  19A116114P2047  19A116114P28  5496218P48  19A116114P32  19A116952P26  5494481P11  5496267P14  7489162P9  19A116952P21  5494481P11  7489162P9  19A116952P21  5494481P11  7489162P9  19A116952P3  5496218P39  19A116952P23	DESCRIPTION  Ceramic disc: 5.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.  Ceramic: 33 pf ±5%, 100 VDCW; temp coef -80 PPM.  Ceramic: 8.2 pf ±5%, 100 VDCW; temp coef 0 PPM.  Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.  Silver mica: 26 pf ±2%, 250 VDCW; sim to Underwood Type JIHF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to MMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Ceramic disc: 24 pf ±5%, 500 VDCW; temp coef 0 PPM.  Silver mica: 24 pf ±5%, 500 VDCW; temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JIHF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 13 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 13 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 13 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JIHF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JIHF.
B219436P1 88079P17 B219456P2 88079P6 B219457P1 88079P18 88079P6 B219457P2 D416451P1 A115329P1 77P330J 77P100J	Contact, electrical: sim to Bead Chain L93-3.  Contact, electrical: sim to Bead Chain L83-3.	C16 C17 C18 C19 C20 C21 C22 C23 C24 C25 C26 C27 C28 C29 C30 C31	19A116114P2047 19A116114P28 5496218P48 19A116114P32 19A116952P26 5494481P11 5496267P14 7489162P9 19A116952P21 5494481P11 7489162P9 19A116952P21 5494481P11 7489162P9 19A116952P13	Coranic: 33 pf ±5%, 100 VDCW; temp coef -80 PPI Ceranic: 8.2 pf ±5%, 100 VDCW; temp coef 0 PPM Ceranic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceranic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.  Silver mica: 26 pf ±2%, 250 VDCW; sim to Underwood Type J1HF.  Ceranic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Ceranic disc: 24 pf ±5%, 500 VDCW; temp coef 0 PPM.  Silver mica: 22 pf ±5%, 500 VDCW; temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceranic disc: 1000 pf ±20%, 1000 VDCW; sim to EMC Type JF Discap.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Underwood Type J1HF.  Ceranic disc: 8.0 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceranic disc: 8.0 pf ±0.5 pf, 500 VDCW; sim to Underwood Type J1HF.  Ceranic disc: 8.0 pf ±0.25 pf, 500 VDCW; temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
B219436P1 88079P17 B219456P2 88079P6 B219457P1 88079P18 88079P6 B219457P2 D416451P1 A115329P1 77P330J 77P100J	Contact, electrical: sim to Bead Chain 183-3.	C17 C18 C19 C20 C21 C22 C23 C24 C25 C26 C27 C28 C29 C30 C31	19A116114P28 5496218P48  19A116114P32 19A116952P26 5494481P11 5496267P14 7489162P9 19A116114P141 5496218P48 19A116952P21 5494481P11 7489162P9 19A116952P1 35496218P39	Coramic: 33 pf ±5%, 100 VDCW; temp coef -80 PPL Ceramic: 8.2 pf ±5%, 100 VDCW; temp coef 0 PPM Ceramic: 8.2 pf ±5%, 500 VDCW; temp coef 0 PPM Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM . Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM. Silver mica: 26 pf ±2%, 250 VDCW; sim to Underwood Type JlHF. Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15. Ceramic disc: 24 pf ±5%, 500 VDCW; temp coef 0 PPM. Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JlHF. Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to Electro Motive Type DM-15. Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15. Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15. Silver mica: 18 pf ±5%, 500 VDCW; sim to Underwood Type JlHF. Ceramic disc: 8.0 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JlHF. Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW; sim to Underwood Type JlHF. Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW; sim to
B219456P1 88079P17 B219456P2 88079P6 B219457P1 88079P18 88079P6 B219457P2 D416451P1 A115329P1 77P330J 77P100J	Coil.  Choke, RF: 12.0 µh ±10%, 1.00 ohms DC res max; sim to Jeffers 4421-8.  Coil.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; six to Jeffers 4411-8.  Coil.  Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max; six to Jeffers 4421-9.  Choke, RF: 10.0 µh ±10%, 0.30 ohms DC res max; six to Jeffers 4421-9.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; six to Jeffers 4411-8.  Coil.  (Part of printed wiring board).	C18 C19 C20 C21 C22 C23 C24 C25 C26 C27 C28 C29 C30 C31	5496218P48  19A116114P32 19A116952P26  5494481P11  5496267P14  7489162P9  19A116114P141 5496218P48  19A116952P21  5494481P11  7489162P9  19A116352P9  19A116352P1  5496218P39	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM.  Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.  Silver mica: 26 pf ±2%, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to BMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Ceramic disc: 24 pf ±5%, 100 VDCW; temp coef -30 PPM.  Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 8.0 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW; temp coef 0 PPM.
B219456P1 88079P17 B219456P2 88079P6 B219457P1 88079P18 88079P6 B219457P2 D416451P1 A115329P1 77P330J 77P100J	Coil.  Choke, RF: 12.0 µh ±10%, 1.00 ohms DC res max; sim to Jeffers 4421-8.  Coil.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; six to Jeffers 4411-8.  Coil.  Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max; six to Jeffers 4421-9.  Choke, RF: 10.0 µh ±10%, 0.30 ohms DC res max; six to Jeffers 4421-9.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; six to Jeffers 4411-8.  Coil.  (Part of printed wiring board).	C19 C20 C21 C22 C23 C24 C25 C26 C27 C28 C29 C30 C31	194116114P32 194116952P26 5494481P11 5496267P14 7489162P9 194116114P141 5496218P48 194116952P21 5494481P11 7489162P9 194116952P13 5496218P39	Coramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.  Silver mica: 26 pf ±2%, 250 VDCW; sim to Underwood Type JIHF.  Coramic disc: 1000 pf ±20%, 1000 VDCW; sim to HMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Coramic disc: 24 pf ±5%, 500 VDCW; temp coef -30 PPM.  Coramic disc: 24 pf ±5%, 500 VDCW; temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JIHF.  Coramic disc: 1000 pf ±20%, 1000 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JIHF.  Coramic disc: 8.0 pf ±0.25 pf, 500 VDCW; sim to Underwood Type JIHF.  Coramic disc: 8.0 pf ±0.25 pf, 500 VDCW; temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
88079P17 B219456P2 88079P6 B219457P1 88079P18 88079P6 B219457P2 D416451P1 A115329P1 77P330J 77P100J	Coil.  Choke, RF: 12.0 µh ±10%, 1.00 ohms DC res max; sim to Jeffers 4421-8.  Coil.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8.  Coil.  Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4421-9.  Choke, RF: 10.0 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8.  Coil.  (Part of printed wiring board).	C20 C21 C22 C23 C24 C25 C26 C27 C28 C29 C30 C31	19A116952P26 5494481P11 5496267P14 7489162P9 19A116114P141 5496218P48 19A116952P21 5494481P11 7489162P9 19A116952P13 5496218P39	Silver mica: 26 pf ±2%, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to EMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Ceramic: 22 pf ±5%, 100 VDCW; temp coef -30 PP Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 8.0 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
88079P17 B219456P2 88079P6 B219457P1 88079P18 88079P6 B219457P2 D416451P1 A115329P1 77P330J 77P100J	Choke, RF: 12.0 µh ±10%, 1.00 ohms DC res max; sim to Jeffers 4421-8.  Coil.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8.  Coil.  Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4421-9.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8.  Coil.  (Part of printed wiring board).	C21 C22 C23 C24 C25 C26 C27 C28 C29 C30 C31	5494481P11 5496267P14 7489162P9 19A116114P141 5496218P48 19A116952P21 5494481P11 7489162P9 19A116952P13 5496218P39	Underwood Type J1HF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to BMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Ceramic: 22 pf ±5%, 100 VDCW; temp coef -30 PP.  Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 8.0 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 8.0 pf ±0.5 pf, 500 VDCW; temp coef 0 PPM.
B219456P2 88079P6 B219457P1 88079P18 88079P6 B219457P2 D416451P1 A115329P1 77P330J 77P100J	sim to Jeffers 4421-8.  Coil.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8.  Coil.  Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4421-9.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8.  Coil.  (Part of printed wiring board).	C22 C23 C24 C25 C26 C27 C28 C29 C30	5496267P14 7489162P9 19A116114P141 5496218P48 19A116952P21 5494481P11 7489162P9 19A116952P13 5496218P39	BMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Ceramic disc: 24 pf ±5%, 100 VDCW; temp coef -30 PPI.  Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JimF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to EMC Type JF Discap.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 13 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JimF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW; sim to Underwood Type JimF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW; temp coef 0 PPM.
88079P6  8219457P1  88079P18  88079P6  8219457P2  D416451P1  A115329P1  77P330J  77P100J	Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sin to Jeffers 4411-8.  Coil.  Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max; sin to Jeffers 4421-9.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sin to Jeffers 4411-8.  Coil.  (Part of printed wiring board).	C23 C24 C25 C26 C27 C28 C29 C30	7489162P9 19A116114P141 5496218P48 19A116952P21 5494481P11 7489162P9 19A116952P13 5496218P39	Sprague Type 150D.  Silver mica: 18 pf ±55, 500 VDCW; sim to Electro Motive Type DM-15.  Ceramic: 22 pf ±55, 100 VDCW; temp coef -30 PPI Ceramic disc: 24 pf ±55, 500 VDCW, temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JIHF.  Ceramic disc: 1000 pf ±205, 1000 VDCW; sim to EMC Type JF Discapp.  Silver mica: 18 pf ±55, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JIHF.  Ceramic disc: 8.0 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JIHF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
88079P18 88079P6 B219457P2 D416451P1 A115329P1 77P330J 77P100J	sis to Jeffers 4411-8.  Coil.  Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max; sis to Jeffers 4421-9.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sis to Jeffers 4411-8.  Coil.  (Part of printed wiring board).	C24 C25 C26 C27 C28 C29 C30	19A116114P141 5496218P48 19A116952P21 5494481P11 7489162P9 19A116952P13 5496218P39	Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Ceramic: 22 pf ±5%, 100 VDCW; temp coef -30 PPI Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JIBF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 13 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JIHF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW; temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
88079P18 88079P6 B219457P2 D416451P1 A115329P1 77P330J 77P100J	Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4421-9.  Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8.  Coil.  (Part of printed wiring board).	C25 C26 C27 C28 C29 C30 C31	5496218P48 19A116952P21 5494481P11 7489162P9 19A116952P13 5496218P39	Ceramic: 22 pf ±5%, 100 VDCW; temp coef -30 PPI.  Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 1000 pf ±20%, 1000 VBCW; sim to EMC Type JF Discap.  Silver mica: 18 pf ±5%, 500 VBCW; sim to Electro Motive Type DM-15.  Silver mica: 13 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VBCW, temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VBCW; sim to
B219457P2 D416451P1 A115329P1 77P330J 77P100J	Choke, RF: 1.00 µh ±10%, 0.30 ohms DC res max; sim to Jeffers 4411-8.  Coil.  (Part of printed wiring board).	C26 C27 C28 C29 C30 C31	19A116952P21 5494481P11 7489162P9 19A116952P13 5496218P39	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef 0 PPM.  Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type Jimf.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to EMC Type JF Discap.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 13 pf ±0.5 pf, 250 VDCW; sim to Underwood Type Jimf.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
B219457P2 D416451P1 A115329P1 77P330J 77P100J	sim to Jeffers 4411-8.  Coil. (Part of printed wiring board).	C27 C28 C29 C30	5494481P11 7489162P9 19A116952P13 5496218P39	Silver mica: 21 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JlHF.  Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to EMC Type JF Discap.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 18 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JlHF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
D416451P1 A115329P1 77F330J 77F100J	(Part of printed wiring board).  TRANSISTORS Silicon, NPN.  RESISTORS Composition: 33 ohms ±5%, 1/2 w.  Composition: 10 ohms ±5%, 1/2 w.	C28 C29 C30	7489162P9 19A116952P13 5496218P39	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 13 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
.77 <b>P330J</b> .77 <b>P100J</b> .78 <b>P2</b> 00J	Silicon, NPN	C28 C29 C30	7489162P9 19A116952P13 5496218P39	BMC Type JF Discap.  Silver mica: 18 pf ±55, 500 VDCW; sim to Electro Motive Type DM-15.  Silver mica: 13 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JlHF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
.77 <b>P330J</b> .77 <b>P100J</b> .78 <b>P2</b> 00J	Silicon, NPN	C29 C30	19A116952P13 5496218P39	Electro Motive Type DM-15.  Silver mica: 13 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JlHF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
.77 <b>P330J</b> .77 <b>P100J</b> .78 <b>P2</b> 00J	Composition: 33 ohms ±5%, 1/2 w. Composition: 10 ohms ±5%, 1/2 w. Composition: 20 ohms ±5%, 1 w.	C30	5496218P39	Underwood Type J1HF.  Ceramic disc: 8.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
77P100J 78P200J	Composition: 33 ohms ±5%, 1/2 w.  Composition: 10 ohms ±5%, 1/2 w.  Composition: 20 ohms ±5%, 1 w.	C31		coef 0 PPM. Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
77P100J 78P200J	Composition: 10 ohms ±5%, 1/2 w.  Composition: 20 ohms ±5%, 1 w.		19A116952P23	Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to Underwood Type JlHF.
		C32		
			7489162P9	Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
7772000		C33	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to
152P243J	Composition: 10 ohms ±5%, 1/2 w.  Composition: 24,000 ohms ±5%, 1/4 w.	C34	5496267P14	RMC Type JF Discap.  Tantalum: 15 µf ±20%, 20 VDCW; sim to
152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	C35	19A116952P23	Sprague Type 150D.  Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
90205P16 77P510J	Composition: 2.7 ohms 15%, 1 w. Composition: 51 ohms 15%, 1/2 w.		ł	Underwood Type J1HF.
.775100	·	C36	5494481P9	Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
A121948G9	RF: 500 VDC, Includes 11-1/2 inch cable	C37*	5496218P44	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef 0 PPM.
	(19B209044P19).		l	Earlier than REV A:
	PA BOARD		5496218P38	Ceramic disc: 7.0 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
	19D416466G1	C38	19A116952P25	Silver mica: 25 pf ±2%, 250 VDCW; sim to Underwood Type JlHF.
A116192P1		C39	5494481P11	Ceramic disc: 1000 pf $\pm 20\%$ , 1000 VDCW; sim to RMC Type JF Discap.
	8121-050-W5R.	C40	7489162P9	Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
A116114P41 A116114P2045	Ceramic: 22 pf ±5%, 100 VDCW; temp coef 0 PPM.  Ceramic: 30 pf ±5%, 100 VDCW; temp coef -80 PPM.	C41	5496267P14	Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.
94481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	C42	19A116952P23	Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to
		C43	5494481P9	Underwood Type J1HF.  Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to
	Sprague Type 150D.	1	1	RMC Type JF Discap.  Ceramic disc: 15 pf ±5%. 500 VDCW, temp coef
A116114P12 89162 <b>D</b> 9	Ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM.			O PPM.
	Electro Motive Type DM-15.		5496218P38	Earlier than REV A: Ceramic disc: 7.0 pf ±0.25 pf, 500 VDCW, temp
A116114P12 A116114P32		C45		coef 0 PPM. Silver mica: 25 pf ±2%, 250 VDCW; sim to
A116114P41	Ceramic: 22 pf ±5%, 100 VDCW; temp coef 0 PPM.			Underwood Type JlHF.
A116114P32	Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.	C46	ļ	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
A116114P141	Ceramic: 22 pf ±5%, 100 VDCW; temp coef -30 PPM.  Ceramic: 27 nf +5% 100 VDCW; temp coef 0 PPM.	C47	5496267P14	Tantalum: 15 $\mu f$ $\pm 20\%$ , 20 VDCW; sim to Sprague Type 150D.
A116114044	John S. p. 100, 100 then, temp coef o FFE.	C48	7489162P9	Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
A116114P44	l l	1	1	1
96 A1 89 A1 A1	267P14 16114P12 162P9 16114P12 16114P32 16114P41 16114P32 16114P32	481P11 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  267P14 Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 1500.  16114P12 Ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM.  162P9 Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  16114P12 Ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P32 Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P41 Ceramic: 22 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P32 Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P34 Ceramic: 22 pf ±5%, 100 VDCW; temp coef 0 PPM.	481P11 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  287P14 Tantalum: 15 pf ±20%, 20 VDCW; sim to Sprague Type 150D.  16114P12 Ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM.  162P9 Silver mica: 18 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.  16114P12 Ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P32 Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P41 Ceramic: 22 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P32 Ceramic: 22 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P44 Ceramic: 22 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P44 Ceramic: 27 pf ±5%, 100 VDCW; temp coef 0 PPM.	481P11 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.  287P14 Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D.  Ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P12 Ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P12 Ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P12 Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P32 Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P41 Ceramic: 22 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P41 Ceramic: 22 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P44 Ceramic: 27 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P44 Ceramic: 27 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P44 Ceramic: 27 pf ±5%, 100 VDCW; temp coef 0 PPM.  16114P44 Ceramic: 27 pf ±5%, 100 VDCW; temp coef 0 PPM.

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	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
	C49	19A116952P23	Silver mica: 23 pf ±0.5 pf, 250 VDCW; sim to Underwood Type J1HF.	R4 thru R7	3R77P100J	Composition: 10 ohms ±5%, 1/2 w.
l	C50	5494481P9	Ceramic disc: 680 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	R8	3R78P101J	Composition: 100 ohms ±5%, 1 w.
١	C51	19A116114P2047	Ceramic: 33 pf ±5%, 100 VDCW; temp coef -80 PPM.	R9 and	3R77P100J	Composition: 10 ohms ±5%, 1/2 w.
١	C52	19A116114P28	Ceramic: 8.2 pf ±5%, 100 VDCW; temp coef 0 PPM.	R10 R11	3R78P101J	Composition: 100 ohms ±5%, 1 w.
ı	C53	19A116114P32	Ceramic: 10 pf ±5%, 100 VDCW; temp coef 0 PPM.	R12	3R77P100J	Composition: 10 ohms 15%, 1 w. Composition: 10 ohms ±5%, 1/2 w.
l	C54	19A116288P17	Ceramic: 100 pf ±5%, 200 VDCW; sim to Erie 8121-A200-COG-101J.	, m	Jan Proce	
١	C55	19A116114P28	Ceramic: 8.2 pf ±5%, 100 VDCW; temp coef 0 PPM.		19A121948G10	RF: 500 VDC. Includes 2 inch cable
١	C56	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.			(19B209044P19).
l			DIODES AND RECTIFIERS	W2	19A129234P1	RF: 500 VDC. Includes 5-1/2 inch cable (19B209044P23).
۱	CR1	19A115250P1	Silicon.			CAPACITORS
١			JACKS AND RECEPTACLES	C101	5493392P107	Ceramic, stand off: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type SS5D.
l	Jl thru J8	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	C102 thru C104	5493392P7	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FA5C.
ı			INDUCTORS	C104	5496267D14	Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague
l	Ll	19B209420P125	Coil, RF: 10.0 µh ±10%, 3.10 ohms DC res max; sim to Jeffers 4446-4.	6103	3490207914	Type 150D.
ı	L2	7488079P6	Choke, RF: 1.00 $\mu$ h $\pm$ 10%, 0.30 ohms DC res max; sim to Jeffers 4411-8K.	FL101	19C320050G1	Bandpass.
ı	L3	7488079P16	Choke, RF: 10.0 µh ±10%, 0.60 ohms DC res max; sim to Jeffers 4421-7K.	FL102	19C320051G1	Bandpass,
ļ	14	19A129233P1	Coil.	FL103	19C320088G1	Lowness
١	1.5	7488079P18	Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max;	1		
١			sim to Jeffers 4421-9K.	1		JACKS AND RECEPTACLES
١	L6	7488079P40	Choke, RF: 5.60 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4422-1K.	J101	19C303426G1	Connector: 20 pin contacts.
١	L7	19B219457P3	Coil.	3102	198203689GI	Jack: 16 contacts, includes (16) 19A115853P1 contacts.
١	L8	7488079P18	Choke, RF: 15.0 $\mu h$ ±10%, 1.20 ohms DC res max; sim to Jeffers 4421-9K.			TRANSISTORS
ı	L9	19B219457P3	Coil.	Q101	19A129181P1	Silicon, NPN.
ı	L10	7488079P40	Choke, RF: 5.60 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4422-1K.	i		RESISTORS
l	LII	7488079P18	Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4421-9K.	R101	19A127071P1	Strap.
١	L12	19B219457P3	Coil.	R102	19A127071P1	Part of Mechanical Parts, consists of:
l	L13	7488079P40	Choke, RF: 5.60 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4422-1K.		19A127071P1 19A127073P1	Strap, item 22. Slide, item 19.
	Ll4 and Ll5	7488079P18	Choke, RF: 15.0 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4421-9K.	R103	19B209022P89	Wirewound: 0.1 ohms ±5%, 2 w; sim to IRC Type BWH.
ļ	L16	19B219457P3	Coil.	ł		SWITCHES
١	L17	7488079P40	Choke, RF: 5.60 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4422-1K.	8101	4031922P1	Push: SPST, normally open, 1/2 amp at 12 VDC; sim to Stackpole Type SS-15.
ı	r78	19B219457P3	Coil.			
	L19	7488079P40	Choke, RF: 5.60 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4422-1K.	W101	19B219822G1	RF: approx 18 inches long.
	L20 thru L37	19D416515P1	(Part of printed wiring board).			HARNESS ASSEMBLY
١			TRANSISTORS			HARNESS ASSEMBLY 19D416431G3 (Includes C105, J101, J102)
1	Q1	19A129283P1	Silicon, NPN.	1	1	I.

19A129283P2

19A129283P4

3R152P682J

Silicon, NPN.

----- RESISTORS -----

Composition: 100 ohms ±5%, 1/2 w.

Composition: 6800 ohms ±5%, 1/4 w.

# **PRODUCTION CHANGES**

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

SYMBOL | GE PART NO.

19B205206G3 19A122805G3 7878455P2

19C311781P1

4035439Pl

19A129212P1

19A129212P2

19B201074P210

19B201074P304

19A127177G2

4036555P1

19A127073P1

19A129179P2

5491595P9

4036928P2

19B205884G2

5492178P2

MECHANICAL PARTS (SEE RC-2328)

Nut, sheet spring: sim to Tinnerman C6452-8Z-67.

Contact electrical. (Used with J101).

Clip, spring tension.

7160861P4

19A116065P1

19B201074P206

Heat sink.

N170P16006P2 Cap screw: No. 10-32 x 3/8.

DESCRIPTION

Tap screw, Phillips Pozidriv: No. 4-40-3/8.

Tap screw, Phillips Pozidriv: No. 4-40-5/8.

Shield, electronic. (Used with J2 on FL103, W2 on A103).

Washer, spring tension: sim to Wallace Barnes 375-20. (Used with Q1-Q6 on AlO3).

Hex nut: No. 8-32. (Used with Q1-Q6 on A103).

Insulator, disc. (Used with Q1 on A102).

Heat sink. (Used with Q1 on A105).

Plate. (Used with Q101).

Screw, tap: No. 6-32 x 1/4.

Slide. (Part of R102).

19A127071P1 Strap. (R101 and part of R102).

Retaine(Not Used).

Grommet, plastic.

19B201074P305 | Screw, tap: No. 6-32 x 5/16.

N44P9005Cl3 Screw: No. 4-40 x 5/16.

19B207074P204 Tap screw, Phillips Pozidriv: 4-40 x 1/4.

Plate, with cutout. (Used with Q101).

To improve power output at the low end of the band and to prevent exciter relay operation in unkeyed mode. Changed C37 and C44.

REV. B - PA Board 19D416431G2

To prevent Squelch of the receiver due to feedback. Added CR102.

19B201074P206 Screw, Phillips Pozidriv: 4-40-3/8. 19D416488P1 Heat sink. 23 22 21 20 19 18 17 16 15 13 12 Solderless terminal; sim to Shakeproof 2177-04-000. 9 25 26 27

## **ORDERING SERVICE PARTS**

Each component appearing on the schematic diagram is identified by a symbol number, to simplify locating it in the parts list. Each component is listed by symbol number, followed by its description and GE Part No.

Service parts may be obtained from Authorized GE Communication Equipment Service Stations or through any GE Radio Communication Equipment Sales Office. When ordering a part, be sure to give:

- 1. GE Part Number for component
- 2. Description of part
- 3. Model number of equipment
  4. Revision letter stamped on unit

These instructions do not purport to cover all details or variations in equipment nor to provide for every possible contingency to be met in connection with installation, operation or maintenance.

Should further information be desired, or should particular problems arise which are not covered sufficiently for the purchaser's purposes, contact the nearest Radio Communication Equipment Sales Office of the General Electric Company.

LBI-4386

MOBILE RADIO DEPARTMENT
GENERAL ELECTRIC COMPANY • LYNCHBURG, VIRGINIA 24502

